Hermetic Infrared Emitting Diode

Electronics

OP123, OP124, OP223, OP224

Features:

- Hermetically sealed package
- Mechanically and spectrally matched to other OPTEK devices
- Designed for direct mount to PCBoard



Description:

Each **OP123** and **OP124** device is a 935 nanometer (nm) high intensity gallium arsenide infrared emitting diode (GaAs), mounted in a miniature hermetically sealed "pill" package with an enhanced temperature range and a high power output. These devices are designed for direct mounting to PCBoards.

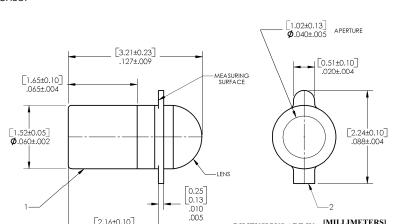
Each OP223 and OP224 device is an 890 nm gallium aluminum arsenide infrared emitting diode (GaAlAs), mounted in a hermetically sealed "pill" package with an enhanced temperature range and a narrow irradiance pattern that provides high on-axis intensity for excellent coupling efficiency. These devices offer significantly higher power output than GaAs at equivalent drive currents and have a wavelength that is matched to silicon's peak response. Their small package size permits high device density mounting.

All these LEDs are mechanically and spectrally matched to the OP300 series, OP600 series and OP640 series devices.

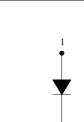
Please refer to Application Bulletins 208 and 210 for additional design information and reliability (degradation) data, and to Application Bulletin 202 for pill-type soldering to PCBoard.

Applications:

- Non-contact reflective object sensor
- Assembly line automation
- Machine automation
- Machine safety
- End of travel sensor
- Door sensor



DIMENSIONS ARE IN: [MILLIMETERS] INCHES



Ordering Information **LED Peak**

Wavelength

935 mm

890 mm

Part

Number

OP123

OP124

OP223

OP224

Total Beam

Angle

24°

Pin #	LED	Sensor		
1	Anode	Collector		
2	Cathode	Emitter		



[2.16±0.10]

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Electrical Specifications

Electrical Specifications									
Absolute	Maximum Ratings (T _A = 25° C unless oth	herwise	noted)						
Storage Temperature Range							-65°C to +150°C		
Operating Temperature Range							-65°C to +125°C		
Revers	2.0 V								
Contin	100 mA								
Peak F	1.0 A								
Lead S	260° C ⁽¹⁾⁽²⁾								
Power	150 mW ⁽³⁾								
Electrica	Characteristics (T _A = 25° C unless otherw	vise no	ted)						
SYMBOL	PARAMETER		TYP	MAX	UNITS	TEST CONDITIONS			
Input Die	ode		I	I		ı			
E _{E (APT)} ⁽³⁾	Apertured Radiant Incidence OP123 OP124 OP223 OP224	0.40 1.00 1.00 3.50	- - -	- - -	mW/cm²	I _F = 50 mA ⁽⁴⁾			
V_{F}	Forward Voltage OP123 OP124	-	-	1.50 1.80	V	I _F = 50 mA			
I_{R}	Reverse Current	-	-	100	μA	V _R = 2.0 V			
$\lambda_{ extsf{P}}$	Wavelength at Peak Emission OP123, OP124 OP223, OP224		935 890		nm	I _F = 50 mA I _F = 10 mA			
В	Spectral Bandwidth between Half Power Points OP123, OP124 OP223, OP224	- -	50 80		nm	I _F = 50 mA I _F = 10 mA			
$\Delta\lambda_{P}/\Delta T$	Spectral Shift with Temperature OP123, OP124 OP223, OP224	- -	+0.30 +0.18		nm/°C	I _F = Constant			
θ_{HP}	Emission Angle at Half Power Points	-	24	-	Degree	I _F = 50 mA			
t _r	Output Rise Time OP123, OP124 OP223, OP224		1000 500		ns	I _{F(PK)} =100 mA, P D.C.=10.0 %	W=10 µs, and		
t _f	Output Fall Time OP123, OP124	-	500	-	ns	I _{F(PK)} =100 mA, PW=10 μs, and D.C.=10.0 %			

Notes:

- 1. Refer to Application Bulletin 202 which reviews proper soldering techniques for pill-type devices.
- 2. No clean or low solids. RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering.
- 3. Derate linearly 1.50 mW/° C above 25° C.
- For OP123, OP124, OP223 and OP224, E_{E(APT)} is a measurement using a 0.031" (0.787 mm) diameter apertured sensor placed 0.50" (12.7 mm) from the measuring surface. $E_{E(APT)}$ is not necessarily uniform within the measured area.

250

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OP223, OP224

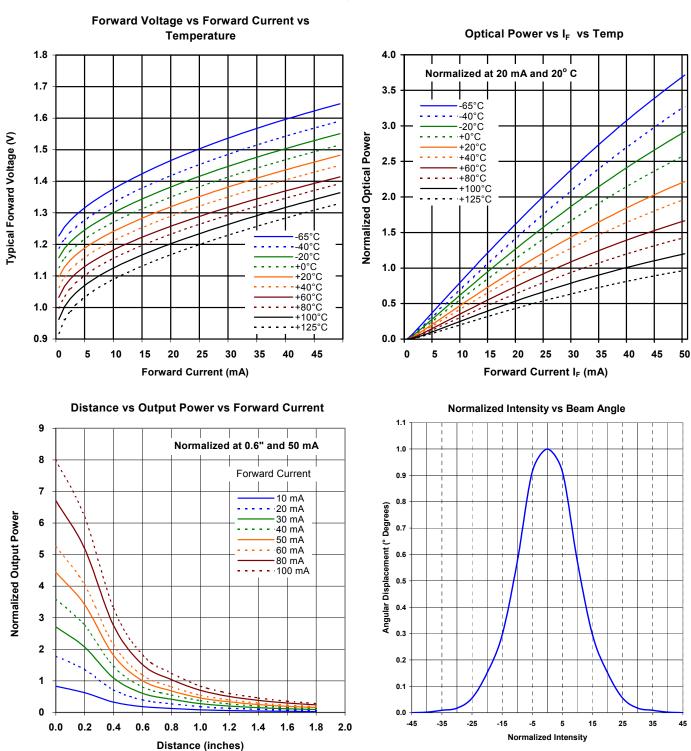
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Performance

OP123, OP124



General Note

TT Electronics reserves the right to make changes in product specification without notice or liability. All information is subject to TT Electronics' own data and is considered accurate at time of going to print.

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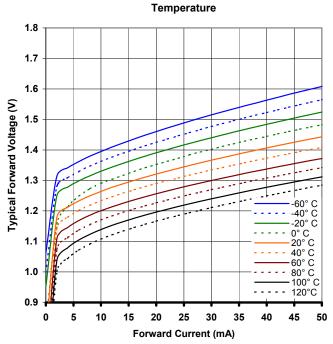
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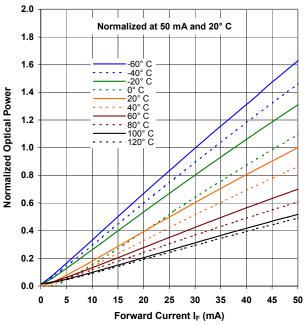
OP123, OP124, OP223, OP224

Performance OP223, OP224

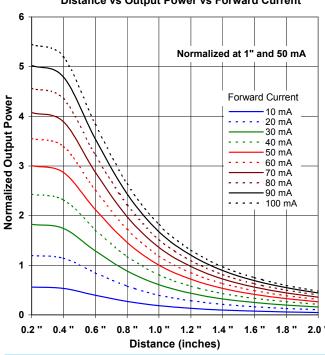
Forward Voltage vs Forward Current vs



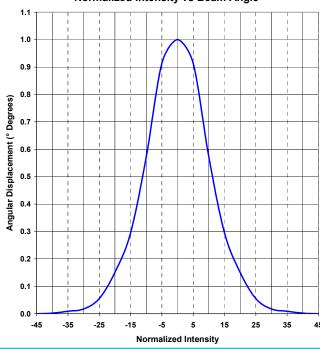
Optical Power vs I_F vs Temperature



Distance vs Output Power vs Forward Current



Normalized Intensity vs Beam Angle



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